

# RJK1555DPA

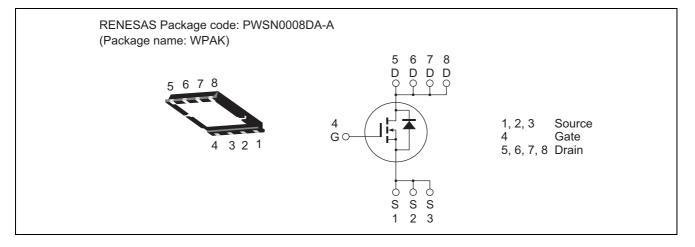
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1783-0100 Rev.1.00 Apr 02, 2009

# Features

- Low on-resistance
- Low drive current
- High density mounting

# Outline



# **Absolute Maximum Ratings**

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	150	V
Gate to source voltage	V <sub>GSS</sub>	±30	V
Drain current	I <sub>D</sub>	25	А
Drain peak current	Note1 I <sub>D (pulse)</sub>	50	А
Body-drain diode reverse drain current	I <sub>DR</sub>	25	А
Body-drain diode reverse drain peak current	Note1 I <sub>DR (pulse)</sub>	50	А
Avalanche current	I <sub>AP</sub> <sup>Note3</sup>	22	А
Avalanche energy	E <sub>AR</sub> <sup>Note3</sup>	36.3	mJ
Channel dissipation	Pch Note2	30	W
Channel to case thermal impedance	θch-c	4.17	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1.  $PW \le 10 \ \mu s$ , duty cycle  $\le 1\%$ 

2. Value at Tc = 25°C

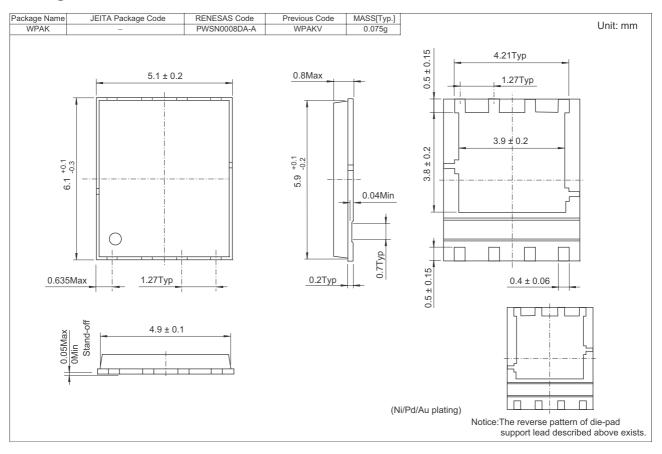
3. STch =  $25^{\circ}$ C, Tch  $\leq 150^{\circ}$ C

# **Electrical Characteristics**

						$(Ta = 25^{\circ}C)$
ltem	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	150	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	—	1	μΑ	$V_{DS} = 150 \text{ V}, \text{ V}_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±1	μΑ	$V_{GS} = \pm 30 \text{ V}, \text{ V}_{DS} = 0$
Gate to source cutoff voltage	V <sub>GS(off)</sub>	2.5	_	4.5	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Static drain to source on state resistance	R <sub>DS(on)</sub>	_	0.038	0.048	Ω	$I_D = 12.5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss	_	2400	_	pF	V <sub>DS</sub> = 25 V
Output capacitance	Coss	_	295	_	pF	V <sub>GS</sub> = 0 f = 1 MHz
Reverse transfer capacitance	Crss	_	69	_	pF	
Turn-on delay time	t <sub>d(on)</sub>	_	32	—	ns	$I_D = 12.5 \text{ A}$ $V_{GS} = 10 \text{ V}$ $R_L = 6 \Omega$ $Rg = 10 \Omega$
Rise time	tr	_	80	—	ns	
Turn-off delay time	t <sub>d(off)</sub>	_	55	—	ns	
Fall time	t <sub>f</sub>	_	46	—	ns	
Total gate charge	Qg	_	38	—	nC	$V_{DD} = 120 V$ $V_{GS} = 10 V$ $I_D = 25 A$
Gate to source charge	Qgs	_	13.6	—	nC	
Gate to drain charge	Qgd	_	10.2		nC	
Body-drain diode forward voltage	V <sub>DF</sub>	_	0.95	1.45	V	$I_F = 25 \text{ A}, V_{GS} = 0^{Note4}$
Body-drain diode reverse recovery time	t <sub>rr</sub>	_	120	_	ns	$I_F = 25 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Notes: 4. Pulse test

# **Package Dimensions**



# **Ordering Information**

Part No.	Quantity	Shipping Container
RJK1555DPA-00-J0	2500 pcs	Taping

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